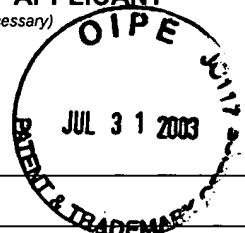


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Application Number	09/691004
Filing Date	October 18, 2000
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Mondt, Johannes

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Attorney Docket No: 303.324US4

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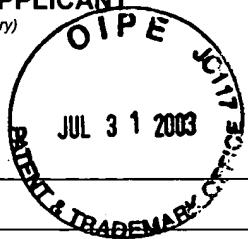
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